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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Yeo, *et al.*	Docket No.:	TSM03-0553
Serial No.:	10/667,871	Art Unit:	2811
Filed:	September 22, 2003	Examiner:	TBD
For:	Resistor With Reduced Leakage		

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Respectfully submitted,

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The Applicant wishes to bring to the attention of the Patent and Trademark Office the information noted on the enclosed form PTO/SB/08A & 08B that may be considered material to the examination of the above-identified application.

No fee is due at this time, as this Information Disclosure Statement is being filed pursuant to 37 C.F.R. § 1.97(b)(3), before the mailing of a first Office action on the merits. If any fee is required, please charge any additional amount, or credit any overpayment to Deposit Acct. No 50-1065 of the below mentioned firm..

Respectfully submitted,

May 26, 2004
Date

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	1	of	3

Complete if Known	
Application Number	10/667,871
Filing Date	September 22, 2003
First Named Inventor	Yeo, *et al.*
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Attorney Docket Number	TSM03-0553

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Examiner Initials*	Cite No.[1]	Document Number Number - Kind Code[2] (*if known*)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Sheet	2	of	3

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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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